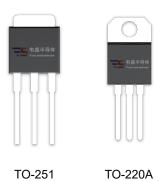


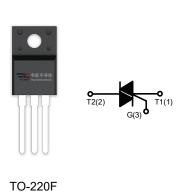
DESCRIPTION:

The BTA06-600C SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	6	А
V _{DRM} /V _{RRM}	600/800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit	
Storage junction temperature range		T _{stg}	-40 - 150	$^{\circ}$ C	
Operating junction temperature range			Tj	-40 - 125	$^{\circ}$ C
Repetitive peak off-state voltage (T _j =25℃)			V _{DRM}	600/800	V
Repetitive peak reverse voltage (T _j =25°C)		V _{RRM}	600/800	V	
RMS on-state current	-	F(Ins)/ (Tc=100℃) A(Non-Ins)	I _{T(RMS)}	6	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I _{TSM}	60	А	
I ² t value for fusing (tp=10ms)			l ² t	18	A ² s
Critical rate of rise of on-state		al/alt	50	Λ/110	
current (I _G =2×I _{GT})		IV	dl/dt	10	A/µs



Peak gate current	l _{GM}	2	Α
Average gate power dissipation	P _{G(AV)}	1	W
Peak gate power	P _{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				С	В	Unit
I _{GT}	V _D =12V R _L =30Ω	I - II -III	MAX	25	50	mA
		IV		50	70	
V _{GT}		ALL	MAX	1.5		V
V _{GD}	$V_D = V_{DRM} T_j = 125$ °C $R_L = 3.3$ KΩ	ALL	MIN	0.2		V
IL IG=1.2IGT	1 -4 01	I -III-IV	MAX	50	70	mA
	IG=1.ZIGT	II	IVIAA	60	80	MA
I _H	I _{TM} =0.2A		MAX	40	60	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	200	500	V/µs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V _{TM}	I _{тм} =8.5A tp=380µs	T _j =25℃	1.5	V
IDRM	V _D =V _{DRM} V _R =V _{RRM}	Tj=25℃	5	μA
I _{RRM}		Tj=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)} junction to case(AC)		TO-220A(Ins) TO-220F(Ins)	2.9	
	TO-220A(Non-Ins) 2.3		°C/W	
		TO-251	2.7	



FIG.1: Maximum power dissipation versus RMS on-state current

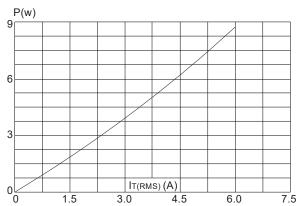


FIG.3: Surge peak on-state current versus number of cycles

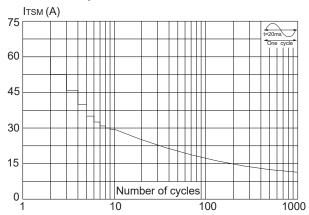


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (I - II - III: dl/dt < 50A/ μ s; IV: dl/dt < 10A/ μ s)

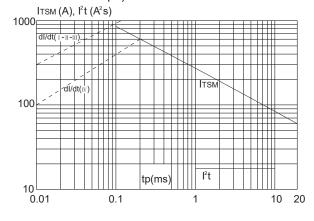


FIG.2: RMS on-state current versus case temperature

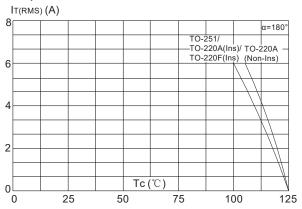


FIG.4: On-state characteristics (maximum values)

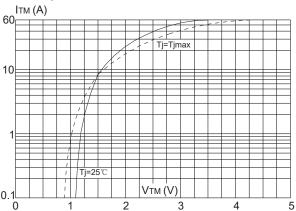


FIG.6: Relative variations of gate trigger current versus junction temperature

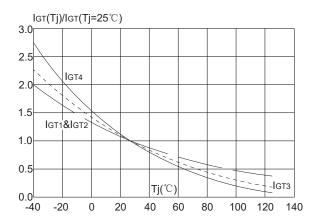




FIG.7: Relative variations of holding current versus junction temperature

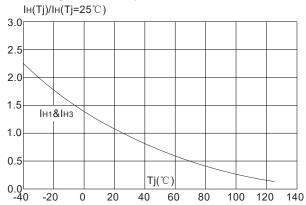


FIG.8: Relative variations of latching current versus junction temperature

